

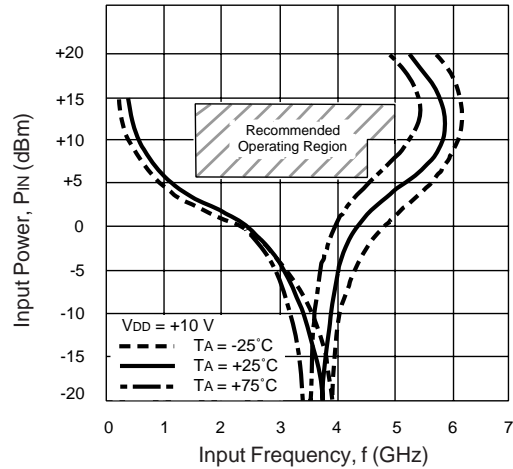
### FEATURES

- **WIDE OPERATING FREQUENCY RANGE:**  
 $f_{IN} = 1.5 \text{ GHz to } 5 \text{ GHz}$  ( $T_A = 25^\circ\text{C}$ )
- **SINGLE SUPPLY VOLTAGE:**  $V_{DD} = +10 \text{ V}$
- **DIVISION RATIO OF 4**
- **HIGH RELIABILITY HERMETICALLY SEALED PACKAGE**
- **GUARANTEED PERFORMANCE OVER AN AMBIENT TEMPERATURE RANGE:**  $-25^\circ\text{C to } +75^\circ\text{C}$

### DESCRIPTION

The UPG501B is a GaAs divide-by-4 prescaler that is capable of operating up to 5 GHz. It is intended to be used in frequency synthesizers of microwave communications systems and measurement equipment. The UPG501B is a static divider with two (2) master-slave D-type flip-flops using Source-Coupled-FET-Logic (SCFL). It operates from a single supply voltage. The UPG501B is housed in a hermetically sealed 8-lead ceramic flat package that is easy to use and provides high reliability.

INPUT POWER vs. INPUT FREQUENCY



### ELECTRICAL CHARACTERISTICS ( $T_A = -25^\circ\text{C to } +75^\circ\text{C}$ , $V_{DD} = 10 \text{ V}$ , $V_{GG} = \text{Open}$ )

PART NUMBER PACKAGE OUTLINE			UPG501B BF08		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
$I_{DD}$	Supply Current	mA	50	70	90
$f_{IN(U)}$	Upper Limit of Input Frequency	GHz	5.0	5.3	
$f_{IN(L)}$	Lower Limit of Input Frequency	GHz		0.7	1.5
$P_{IN}$	Input Power, $f_{IN} = 4.5 \text{ to } 5 \text{ GHz}$	dBm	10.0		13.0
	$f_{IN} = 1.5 \text{ to } 4.5 \text{ GHz}$	dBm	6.0		13.0
$P_{OUT}$	Output Power at $f_{IN} = 5 \text{ GHz}$	dBm	-1.0	2.0	
$R_{TH(CH-C)}$	Thermal Resistance (Channel to Case)	$^\circ\text{C/W}$			16

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>** (T<sub>A</sub> = 25°C)

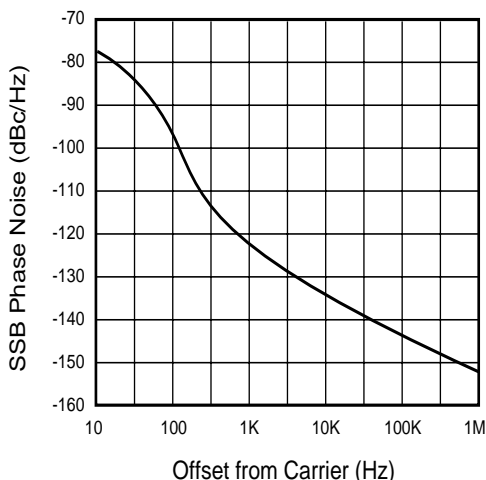
SYMBOLS	PARAMETERS	UNITS	RATINGS
V <sub>DD</sub>	Supply Voltage	V	+12
I <sub>DD</sub>	Supply Current	mA	150
P <sub>T</sub>	Total Power Dissipation <sup>2</sup>	W	1.5
P <sub>IN</sub>	Input Power	dBm	+20
T <sub>OP</sub>	Operating Temperature	°C	-65 to +125
T <sub>STG</sub>	Storage Temperature	°C	-65 to +175

Notes:

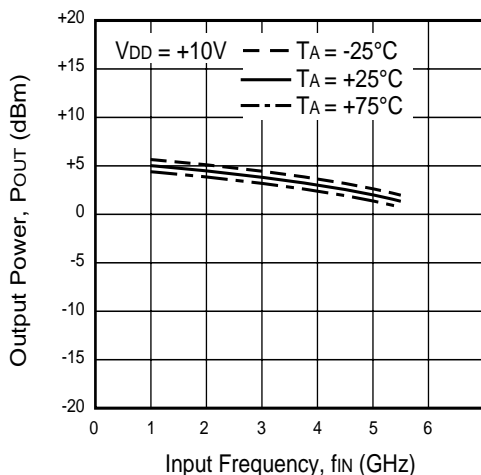
1. Operation in excess of any one of these conditions may result in permanent damage.
2. T<sub>C</sub> ≤ 125°C

**TYPICAL PERFORMANCE CURVES** (T<sub>A</sub> = 25°C)

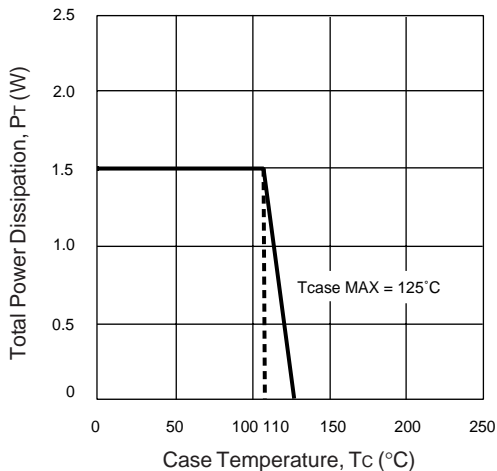
**SSB PHASE NOISE vs. OFFSET FROM CARRIER**  
f<sub>IN</sub> = 3.41 GHz, T<sub>A</sub> = 25°C



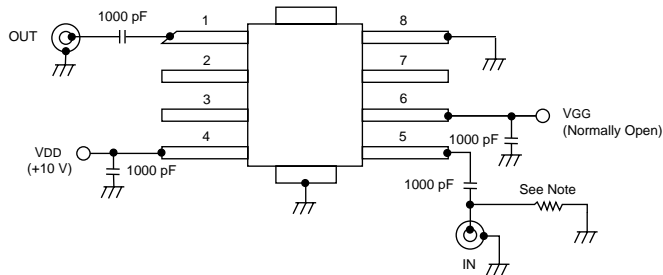
**OUTPUT POWER vs. INPUT FREQUENCY**



**POWER DERATING CURVE**



**TEST CIRCUIT**



Note: Because of the high internal gain and gain compression of the UPG501B, the device is subject to self-oscillation in the absence of an RF input signal. This self-oscillation can be suppressed by either of the following means:

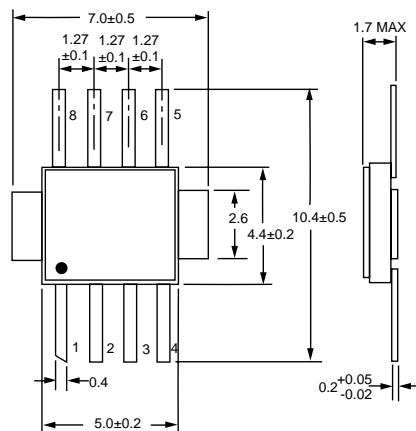
- Add a shunt resistor to the RF input line. Typically a resistor value between 50 and 1000 ohms will suppress the self-oscillation (see the test circuit).
- Apply a negative voltage through a 1000 ohm resistor to the normally open VGG connection. Typically voltages between 0 and -9 volts will suppress the self-oscillation.

Both of these approaches will reduce the input sensitivity of the device (by as much as 3 dB for a 50 ohm shunt resistor), but otherwise have no effect on the reliability or other electrical characteristics of the device.

**OUTLINE DIMENSIONS** (Units in mm)

**UPG501B**

**PACKAGE OUTLINE BF08**



- LEAD CONNECTIONS:**
1. OUTPUT
  2. NC\*
  3. NC\*
  4. V<sub>DD</sub>
  5. INPUT
  6. V<sub>GG</sub>
  7. NC\*
  8. GND
- FLANGE, GND
- \* No connection

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